

## IGBT

TRENCHSTOP™ 5 high Speed soft switching IGBT with full current rated RAPID 1 diode

## IKW40N65ES5

650V TRENCHSTOP™ 5 high speed soft switching duopak

Data sheet

## TRENCHSTOP™ 5 high speed soft switching IGBT copacked with full current rated RAPID 1 fast and soft antiparallel diode

### Features and Benefits:

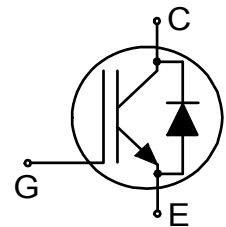
- High speed S5 technology offering
- High speed smooth switching device for hard & soft switching
- Very Low  $V_{CEsat}$ , 1.35V at nominal current
- Plug and play replacement of previous generation IGBTs
- 650V breakdown voltage
- Low gate charge  $Q_G$
- IGBT copacked with full rated RAPID 1 fast antiparallel diode
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:  
<http://www.infineon.com/igbt/>

### Applications:

- Resonant converters
- Uninterruptible power supplies
- Welding converters
- Mid to high range switching frequency converters

### Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



### Key Performance and Package Parameters

| Type        | $V_{CE}$ | $I_C$ | $V_{CEsat}$ , $T_{vj}=25^\circ\text{C}$ | $T_{vjmax}$ | Marking | Package    |
|-------------|----------|-------|-----------------------------------------|-------------|---------|------------|
| IKW40N65ES5 | 650V     | 40A   | 1.35V                                   | 175°C       | K40EES5 | PG-TO247-3 |

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## Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter                                                                                                            | Symbol      | Value                | Unit               |
|----------------------------------------------------------------------------------------------------------------------|-------------|----------------------|--------------------|
| Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$                                                          | $V_{CE}$    | 650                  | V                  |
| DC collector current, limited by $T_{vjmax}$<br>$T_C = 25^{\circ}\text{C}$<br>$T_C = 100^{\circ}\text{C}$            | $I_C$       | 79.0<br>50.0         | A                  |
| Pulsed collector current, $t_p$ limited by $T_{vjmax}$                                                               | $I_{Cpuls}$ | 160.0                | A                  |
| Turn off safe operating area<br>$V_{CE} \leq 650\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}$ | -           | 160.0                | A                  |
| Diode forward current, limited by $T_{vjmax}$<br>$T_C = 25^{\circ}\text{C}$<br>$T_C = 100^{\circ}\text{C}$           | $I_F$       | 79.0<br>50.0         | A                  |
| Diode pulsed current, $t_p$ limited by $T_{vjmax}$                                                                   | $I_{Fpuls}$ | 160.0                | A                  |
| Gate-emitter voltage<br>Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )                    | $V_{GE}$    | $\pm 20$<br>$\pm 30$ | V                  |
| Power dissipation $T_C = 25^{\circ}\text{C}$<br>Power dissipation $T_C = 100^{\circ}\text{C}$                        | $P_{tot}$   | 230.0<br>115.0       | W                  |
| Operating junction temperature                                                                                       | $T_{vj}$    | $-40 \dots +175$     | $^{\circ}\text{C}$ |
| Storage temperature                                                                                                  | $T_{stg}$   | $-55 \dots +150$     | $^{\circ}\text{C}$ |
| Soldering temperature,<br>wave soldering 1.6mm (0.063in.) from case for 10s                                          |             | 260                  | $^{\circ}\text{C}$ |
| Mounting torque, M3 screw<br>Maximum of mounting processes: 3                                                        | $M$         | 0.6                  | Nm                 |

## Thermal Resistance

| Parameter                                    | Symbol        | Conditions | Max. Value | Unit |
|----------------------------------------------|---------------|------------|------------|------|
| <b>Characteristic</b>                        |               |            |            |      |
| IGBT thermal resistance,<br>junction - case  | $R_{th(j-c)}$ |            | 0.65       | K/W  |
| Diode thermal resistance,<br>junction - case | $R_{th(j-c)}$ |            | 0.75       | K/W  |
| Thermal resistance<br>junction - ambient     | $R_{th(j-a)}$ |            | 40         | K/W  |

**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

| Parameter                            | Symbol        | Conditions                                                                                                    | Value       |                      |                | Unit    |
|--------------------------------------|---------------|---------------------------------------------------------------------------------------------------------------|-------------|----------------------|----------------|---------|
|                                      |               |                                                                                                               | min.        | typ.                 | max.           |         |
| Static Characteristic                |               |                                                                                                               |             |                      |                |         |
| Collector-emitter breakdown voltage  | $V_{(BR)CES}$ | $V_{GE} = 0V, I_C = 0.20mA$                                                                                   | 650         | -                    | -              | V       |
| Collector-emitter saturation voltage | $V_{CEsat}$   | $V_{GE} = 15.0V, I_C = 40.0A$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 125^{\circ}C$<br>$T_{vj} = 175^{\circ}C$ | -<br>-<br>- | 1.35<br>1.50<br>1.60 | 1.70<br>-<br>- | V       |
| Diode forward voltage                | $V_F$         | $V_{GE} = 0V, I_F = 40.0A$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 125^{\circ}C$<br>$T_{vj} = 175^{\circ}C$    | -<br>-<br>- | 1.45<br>1.42<br>1.39 | 1.70<br>-<br>- | V       |
| Gate-emitter threshold voltage       | $V_{GE(th)}$  | $I_C = 0.40mA, V_{CE} = V_{GE}$                                                                               | 3.2         | 4.0                  | 4.8            | V       |
| Zero gate voltage collector current  | $I_{CES}$     | $V_{CE} = 650V, V_{GE} = 0V$<br>$T_{vj} = 25^{\circ}C$<br>$T_{vj} = 175^{\circ}C$                             | -<br>-      | -<br>1700            | 50<br>-        | $\mu A$ |
| Gate-emitter leakage current         | $I_{GES}$     | $V_{CE} = 0V, V_{GE} = 20V$                                                                                   | -           | -                    | 100            | nA      |
| Transconductance                     | $g_{fs}$      | $V_{CE} = 20V, I_C = 40.0A$                                                                                   | -           | 45.0                 | -              | S       |

**Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified**

| Parameter                                                            | Symbol    | Conditions                                 | Value |      |      | Unit |
|----------------------------------------------------------------------|-----------|--------------------------------------------|-------|------|------|------|
|                                                                      |           |                                            | min.  | typ. | max. |      |
| Dynamic Characteristic                                               |           |                                            |       |      |      |      |
| Input capacitance                                                    | $C_{ies}$ | $V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$      | -     | 2500 | -    | pF   |
| Output capacitance                                                   | $C_{oes}$ |                                            | -     | 71   | -    |      |
| Reverse transfer capacitance                                         | $C_{res}$ |                                            | -     | 9    | -    |      |
| Gate charge                                                          | $Q_G$     | $V_{CC} = 520V, I_C = 40.0A, V_{GE} = 15V$ | -     | 95.0 | -    | nC   |
| Internal emitter inductance<br>measured 5mm (0.197 in.) from<br>case | $L_E$     |                                            | -     | 13.0 | -    | nH   |

**Switching Characteristic, Inductive Load**

| Parameter                                             | Symbol              | Conditions                                                                                                                                                                                                                                                                                                                                                       | Value |      |      | Unit |
|-------------------------------------------------------|---------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------|------|------|------|
|                                                       |                     |                                                                                                                                                                                                                                                                                                                                                                  | min.  | typ. | max. |      |
| IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$ |                     |                                                                                                                                                                                                                                                                                                                                                                  |       |      |      |      |
| Turn-on delay time                                    | $t_{d(\text{on})}$  | $T_{vj} = 25^{\circ}\text{C}$ ,<br>$V_{CC} = 400\text{V}$ , $I_C = 40.0\text{A}$ ,<br>$V_{GE} = 0.0/15.0\text{V}$ ,<br>$R_{G(\text{on})} = 10.0\Omega$ , $R_{G(\text{off})} = 10.0\Omega$ ,<br>$L_{\sigma} = 30\text{nH}$ , $C_{\sigma} = 30\text{pF}$<br>$L_{\sigma}$ , $C_{\sigma}$ from Fig. E<br>Energy losses include “tail” and<br>diode reverse recovery. | -     | 19   | -    | ns   |
| Rise time                                             | $t_r$               |                                                                                                                                                                                                                                                                                                                                                                  | -     | 18   | -    | ns   |
| Turn-off delay time                                   | $t_{d(\text{off})}$ |                                                                                                                                                                                                                                                                                                                                                                  | -     | 130  | -    | ns   |
| Fall time                                             | $t_f$               |                                                                                                                                                                                                                                                                                                                                                                  | -     | 23   | -    | ns   |
| Turn-on energy                                        | $E_{\text{on}}$     |                                                                                                                                                                                                                                                                                                                                                                  | -     | 0.86 | -    | mJ   |
| Turn-off energy                                       | $E_{\text{off}}$    |                                                                                                                                                                                                                                                                                                                                                                  | -     | 0.40 | -    | mJ   |
| Total switching energy                                | $E_{\text{ts}}$     |                                                                                                                                                                                                                                                                                                                                                                  | -     | 1.26 | -    | mJ   |

|                        |              |                                                                                                                                                                                                                                                                                                                                                 |   |      |   |    |
|------------------------|--------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---|------|---|----|
| Turn-on delay time     | $t_{d(on)}$  | $T_{vj} = 25^{\circ}\text{C}$ ,<br>$V_{CC} = 400\text{V}$ , $I_C = 20.0\text{A}$ ,<br>$V_{GE} = 0.0/15.0\text{V}$ ,<br>$R_{G(on)} = 10.0\Omega$ , $R_{G(off)} = 10.0\Omega$ ,<br>$L_{\sigma} = 30\text{nH}$ , $C_{\sigma} = 30\text{pF}$<br>$L_{\sigma}$ , $C_{\sigma}$ from Fig. E<br>Energy losses include "tail" and diode reverse recovery. | - | 18   | - | ns |
| Rise time              | $t_r$        |                                                                                                                                                                                                                                                                                                                                                 | - | 7    | - | ns |
| Turn-off delay time    | $t_{d(off)}$ |                                                                                                                                                                                                                                                                                                                                                 | - | 143  | - | ns |
| Fall time              | $t_f$        |                                                                                                                                                                                                                                                                                                                                                 | - | 24   | - | ns |
| Turn-on energy         | $E_{on}$     |                                                                                                                                                                                                                                                                                                                                                 | - | 0.39 | - | mJ |
| Turn-off energy        | $E_{off}$    |                                                                                                                                                                                                                                                                                                                                                 | - | 0.21 | - | mJ |
| Total switching energy | $E_{ts}$     |                                                                                                                                                                                                                                                                                                                                                 | - | 0.60 | - | mJ |

#### Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

|                                                                  |              |                                                                                                                           |   |       |   |                  |
|------------------------------------------------------------------|--------------|---------------------------------------------------------------------------------------------------------------------------|---|-------|---|------------------|
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 25^{\circ}\text{C}$ ,<br>$V_R = 400\text{V}$ ,<br>$I_F = 40.0\text{A}$ ,<br>$di_F/dt = 820\text{A}/\mu\text{s}$ | - | 73    | - | ns               |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                           | - | 1.10  | - | $\mu\text{C}$    |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                           | - | 23.0  | - | A                |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                           | - | -1500 | - | A/ $\mu\text{s}$ |
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 25^{\circ}\text{C}$ ,<br>$V_R = 400\text{V}$ ,<br>$I_F = 20.0\text{A}$ ,<br>$di_F/dt = 750\text{A}/\mu\text{s}$ | - | 58    | - | ns               |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                           | - | 0.80  | - | $\mu\text{C}$    |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                           | - | 22.0  | - | A                |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                           | - | -1740 | - | A/ $\mu\text{s}$ |

#### Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value |      |      | Unit |
|-----------|--------|------------|-------|------|------|------|
|           |        |            | min.  | typ. | max. |      |

#### IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

|                        |              |                                                                                                                                                                                                                                                                                                                                                  |   |      |   |    |
|------------------------|--------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---|------|---|----|
| Turn-on delay time     | $t_{d(on)}$  | $T_{vj} = 150^{\circ}\text{C}$ ,<br>$V_{CC} = 400\text{V}$ , $I_C = 40.0\text{A}$ ,<br>$V_{GE} = 0.0/15.0\text{V}$ ,<br>$R_{G(on)} = 10.0\Omega$ , $R_{G(off)} = 10.0\Omega$ ,<br>$L_{\sigma} = 30\text{nH}$ , $C_{\sigma} = 30\text{pF}$<br>$L_{\sigma}$ , $C_{\sigma}$ from Fig. E<br>Energy losses include "tail" and diode reverse recovery. | - | 20   | - | ns |
| Rise time              | $t_r$        |                                                                                                                                                                                                                                                                                                                                                  | - | 16   | - | ns |
| Turn-off delay time    | $t_{d(off)}$ |                                                                                                                                                                                                                                                                                                                                                  | - | 156  | - | ns |
| Fall time              | $t_f$        |                                                                                                                                                                                                                                                                                                                                                  | - | 48   | - | ns |
| Turn-on energy         | $E_{on}$     |                                                                                                                                                                                                                                                                                                                                                  | - | 1.20 | - | mJ |
| Turn-off energy        | $E_{off}$    |                                                                                                                                                                                                                                                                                                                                                  | - | 0.69 | - | mJ |
| Total switching energy | $E_{ts}$     |                                                                                                                                                                                                                                                                                                                                                  | - | 1.89 | - | mJ |
| Turn-on delay time     | $t_{d(on)}$  | $T_{vj} = 150^{\circ}\text{C}$ ,<br>$V_{CC} = 400\text{V}$ , $I_C = 20.0\text{A}$ ,<br>$V_{GE} = 0.0/15.0\text{V}$ ,<br>$R_{G(on)} = 10.0\Omega$ , $R_{G(off)} = 10.0\Omega$ ,<br>$L_{\sigma} = 30\text{nH}$ , $C_{\sigma} = 30\text{pF}$<br>$L_{\sigma}$ , $C_{\sigma}$ from Fig. E<br>Energy losses include "tail" and diode reverse recovery. | - | 18   | - | ns |
| Rise time              | $t_r$        |                                                                                                                                                                                                                                                                                                                                                  | - | 8    | - | ns |
| Turn-off delay time    | $t_{d(off)}$ |                                                                                                                                                                                                                                                                                                                                                  | - | 184  | - | ns |
| Fall time              | $t_f$        |                                                                                                                                                                                                                                                                                                                                                  | - | 48   | - | ns |
| Turn-on energy         | $E_{on}$     |                                                                                                                                                                                                                                                                                                                                                  | - | 0.60 | - | mJ |
| Turn-off energy        | $E_{off}$    |                                                                                                                                                                                                                                                                                                                                                  | - | 0.39 | - | mJ |
| Total switching energy | $E_{ts}$     |                                                                                                                                                                                                                                                                                                                                                  | - | 0.99 | - | mJ |

**Diode Characteristic, at  $T_{vj} = 150^{\circ}\text{C}$** 

|                                                                  |              |                                                                                                                         |   |       |   |                        |
|------------------------------------------------------------------|--------------|-------------------------------------------------------------------------------------------------------------------------|---|-------|---|------------------------|
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 150^{\circ}\text{C},$<br>$V_R = 400\text{V},$<br>$I_F = 40.0\text{A},$<br>$di_F/dt = 820\text{A}/\mu\text{s}$ | - | 120   | - | ns                     |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                         | - | 2.60  | - | $\mu\text{C}$          |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                         | - | 36.0  | - | A                      |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                         | - | -1250 | - | $\text{A}/\mu\text{s}$ |
| Diode reverse recovery time                                      | $t_{rr}$     | $T_{vj} = 150^{\circ}\text{C},$<br>$V_R = 400\text{V},$<br>$I_F = 20.0\text{A},$<br>$di_F/dt = 750\text{A}/\mu\text{s}$ | - | 91    | - | ns                     |
| Diode reverse recovery charge                                    | $Q_{rr}$     |                                                                                                                         | - | 1.80  | - | $\mu\text{C}$          |
| Diode peak reverse recovery current                              | $I_{rrm}$    |                                                                                                                         | - | 32.0  | - | A                      |
| Diode peak rate of fall of reverse recovery current during $t_b$ | $di_{rr}/dt$ |                                                                                                                         | - | -1350 | - | $\text{A}/\mu\text{s}$ |

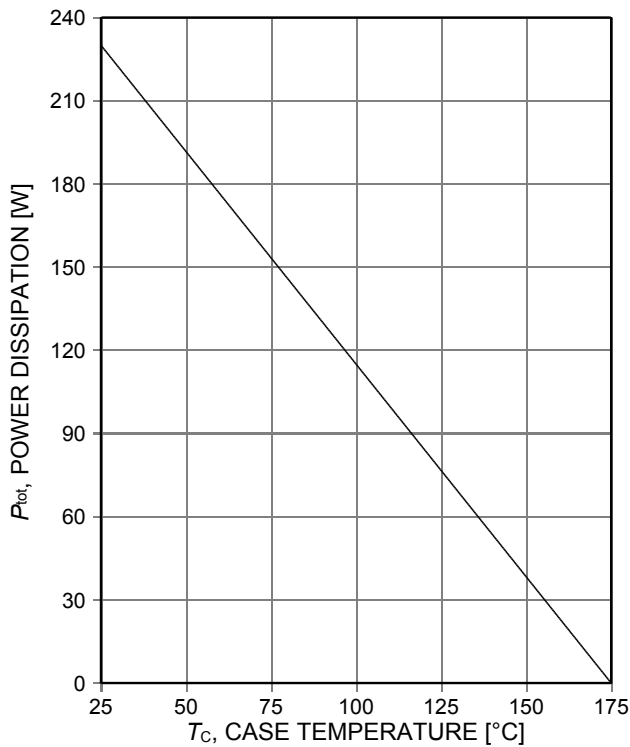


Figure 1. **Power dissipation as a function of case temperature**  
( $T_{vj} \leq 175^\circ\text{C}$ )

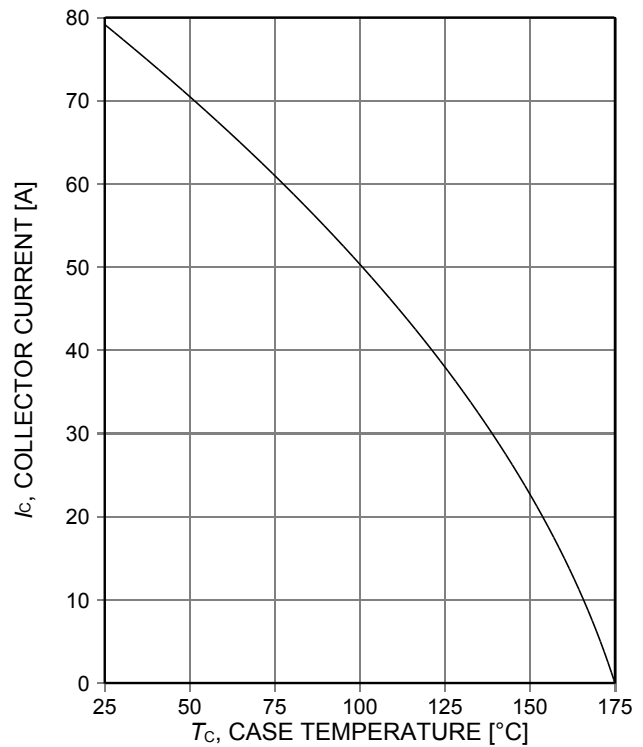


Figure 2. **Collector current as a function of case temperature**  
( $V_{GE} \geq 15\text{V}$ ,  $T_{vj} \leq 175^\circ\text{C}$ )

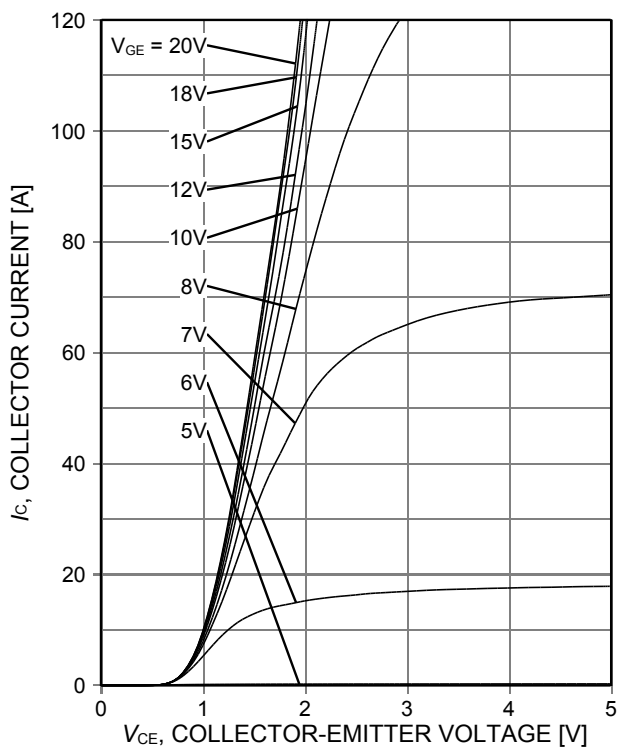


Figure 3. **Typical output characteristic**  
( $T_{vj} = 25^\circ\text{C}$ )

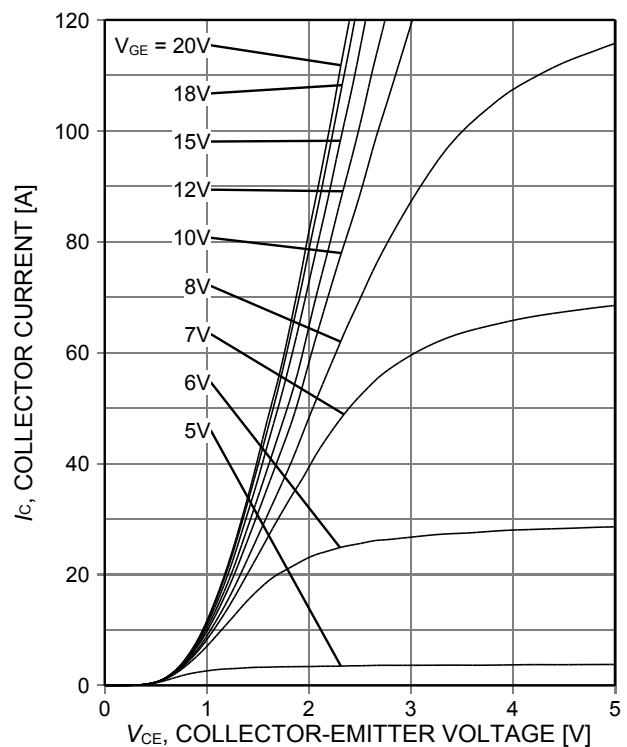


Figure 4. **Typical output characteristic**  
( $T_{vj} = 175^\circ\text{C}$ )

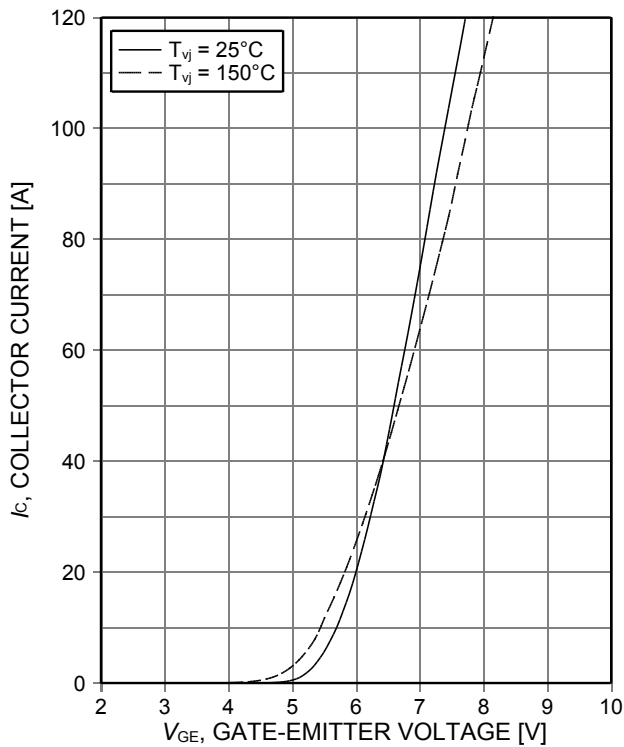


Figure 5. **Typical transfer characteristic**  
( $V_{CE}=20V$ )

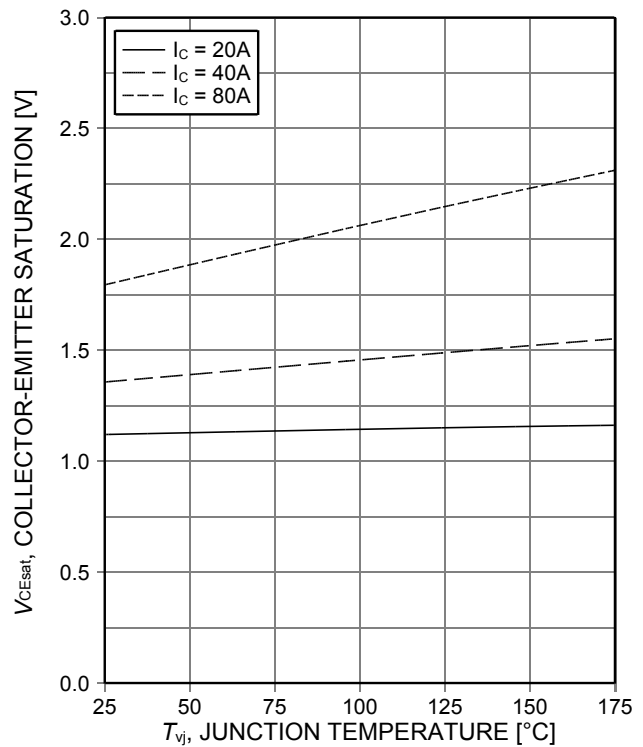


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE}=15V$ )

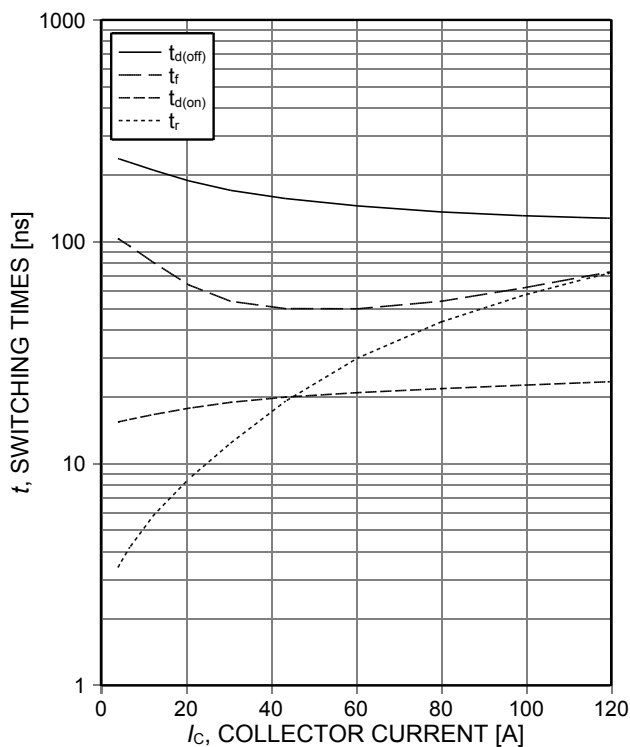


Figure 7. **Typical switching times as a function of collector current**  
(inductive load,  $T_{vj}=150^{\circ}C$ ,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $R_{Gon}=10\Omega$ ,  $R_{Goff}=10\Omega$ , dynamic test circuit in Figure E)

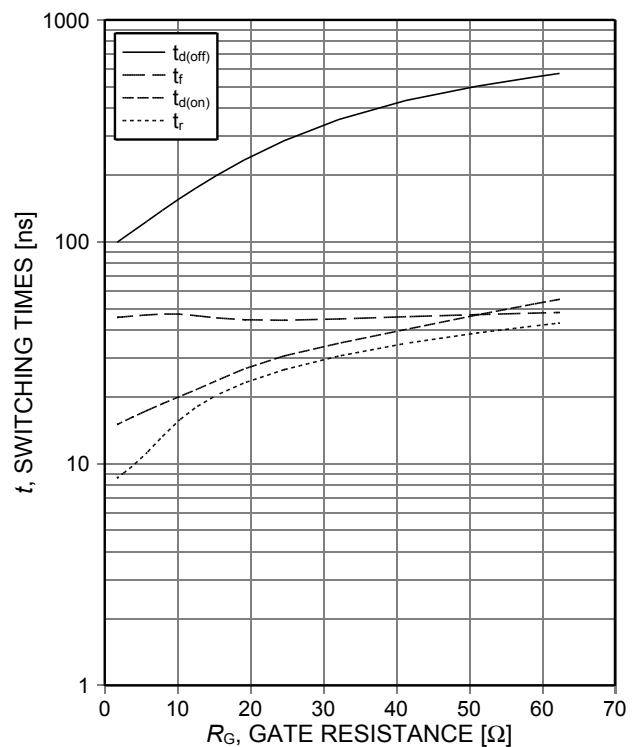


Figure 8. **Typical switching times as a function of gate resistance**  
(inductive load,  $T_{vj}=150^{\circ}C$ ,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $I_C=40A$ , dynamic test circuit in Figure E)

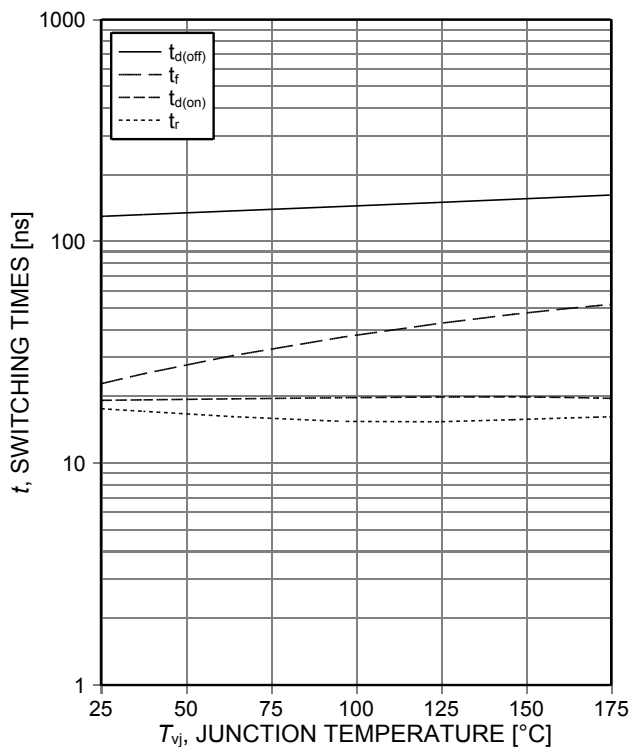


Figure 9. **Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $I_C=40A$ ,  $R_{Gon}=10\Omega$ ,  $R_{Goff}=10\Omega$ , dynamic test circuit in Figure E)

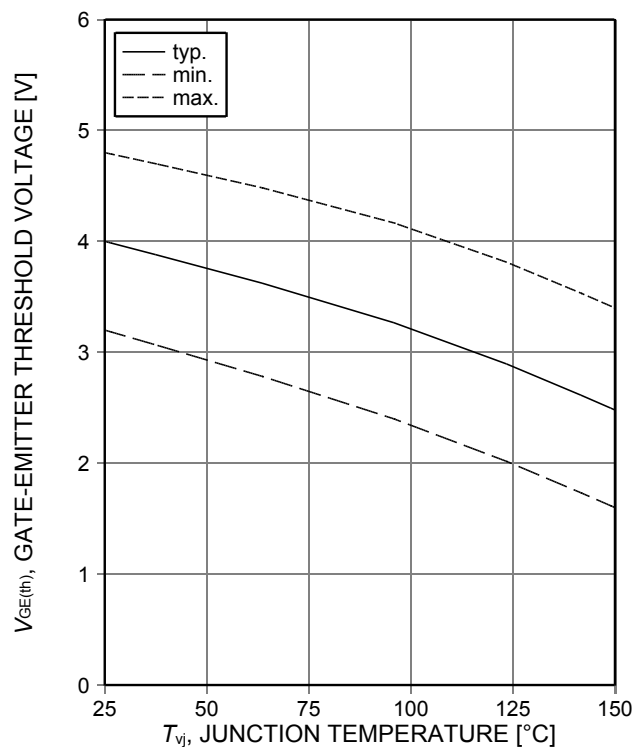


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C=0.4mA$ )

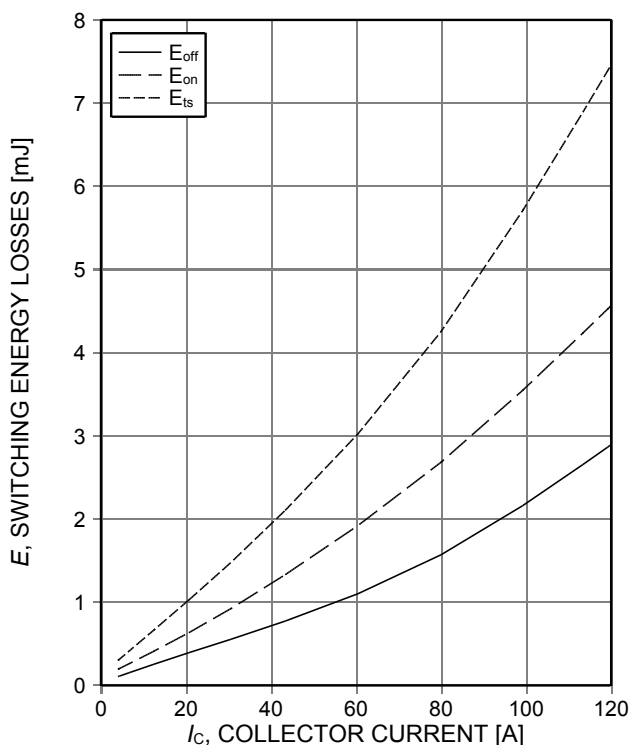


Figure 11. **Typical switching energy losses as a function of collector current**  
(inductive load,  $T_{vj}=150^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $R_{Gon}=10\Omega$ ,  $R_{Goff}=10\Omega$ , dynamic test circuit in Figure E)

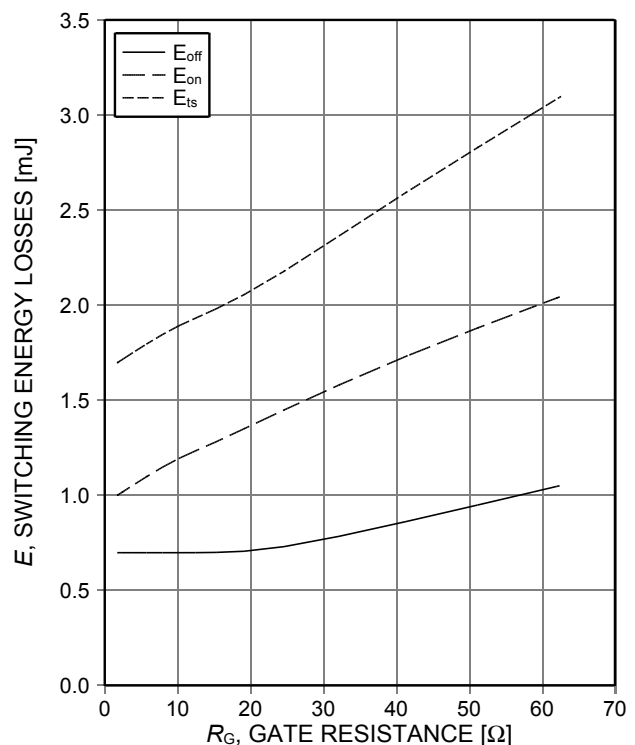


Figure 12. **Typical switching energy losses as a function of gate resistance**  
(inductive load,  $T_{vj}=150^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $I_C=40A$ , dynamic test circuit in Figure E)

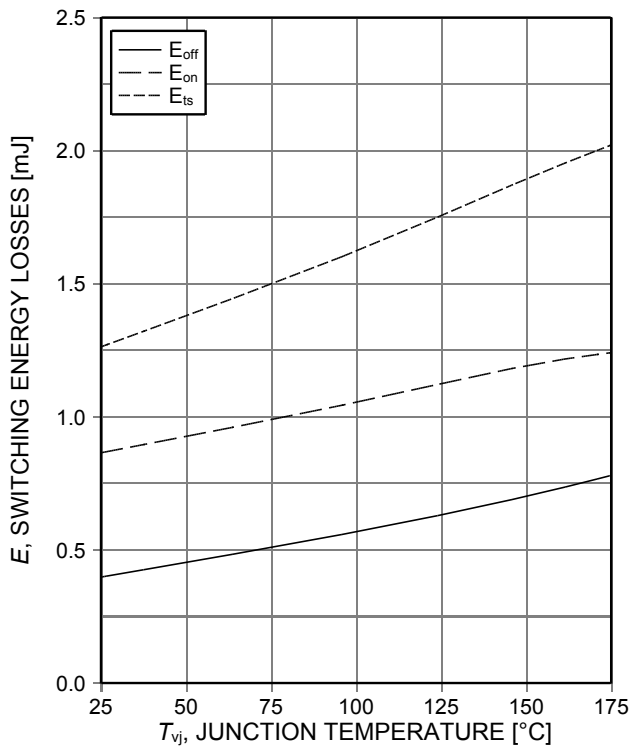


Figure 13. **Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE}=400V$ ,  $V_{GE}=0/15V$ ,  $I_C=40A$ ,  $R_{Gon}=10\Omega$ ,  $R_{Goff}=10\Omega$ , dynamic test circuit in Figure E)

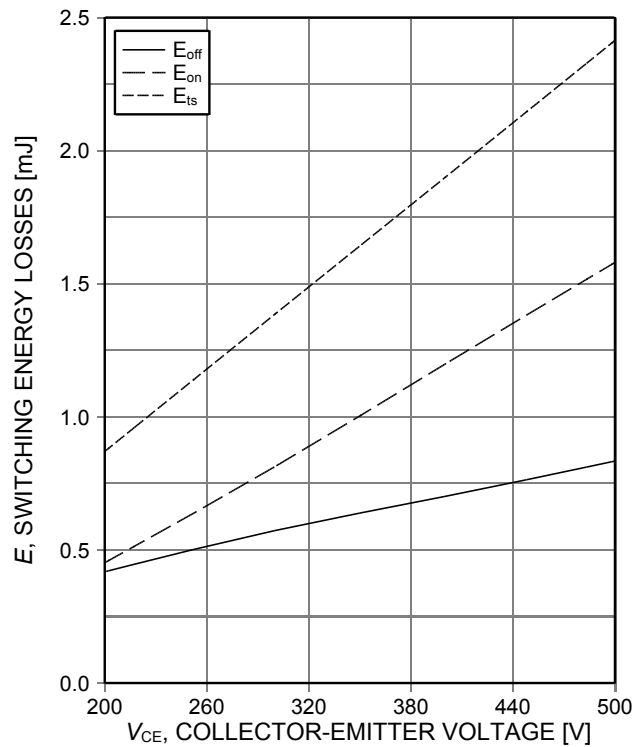


Figure 14. **Typical switching energy losses as a function of collector-emitter voltage**  
(inductive load,  $T_{vj}=150^\circ C$ ,  $V_{GE}=0/15V$ ,  $I_C=40A$ ,  $R_{Gon}=10\Omega$ ,  $R_{Goff}=10\Omega$ , dynamic test circuit in Figure E)

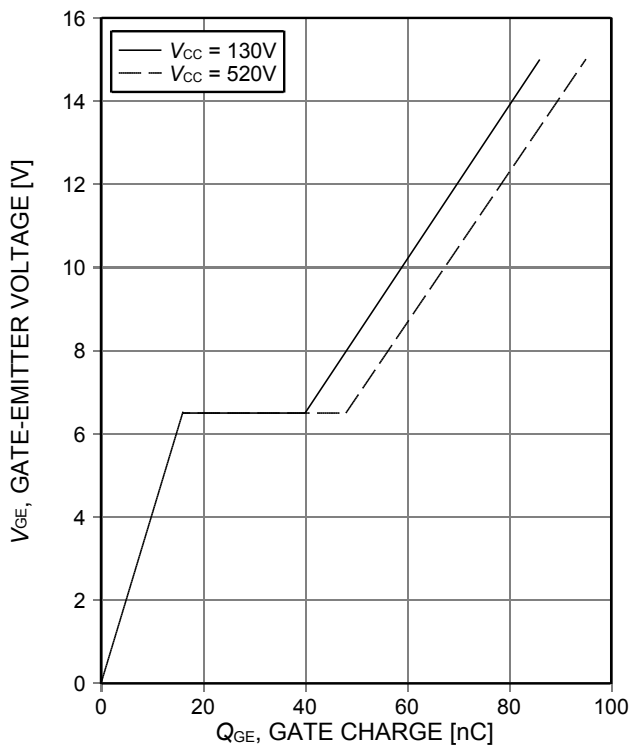


Figure 15. **Typical gate charge**  
( $I_C=40A$ )

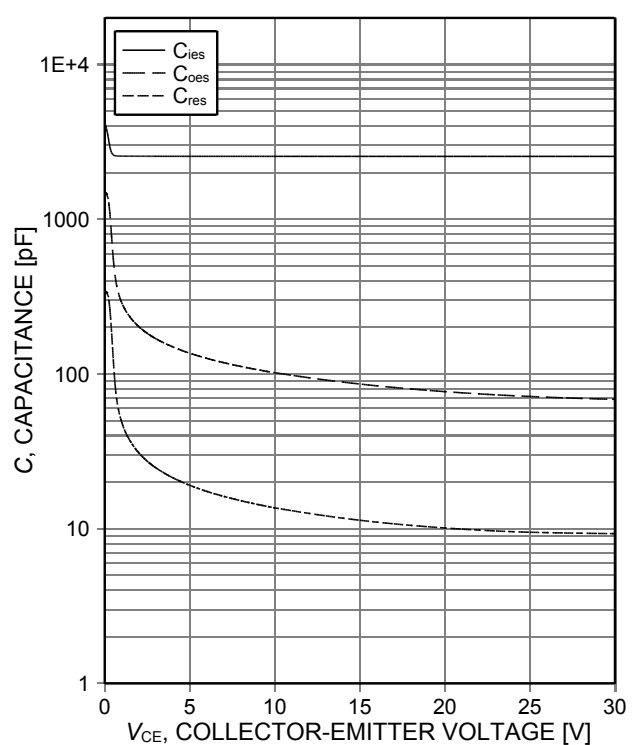


Figure 16. **Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0V$ ,  $f=1MHz$ )

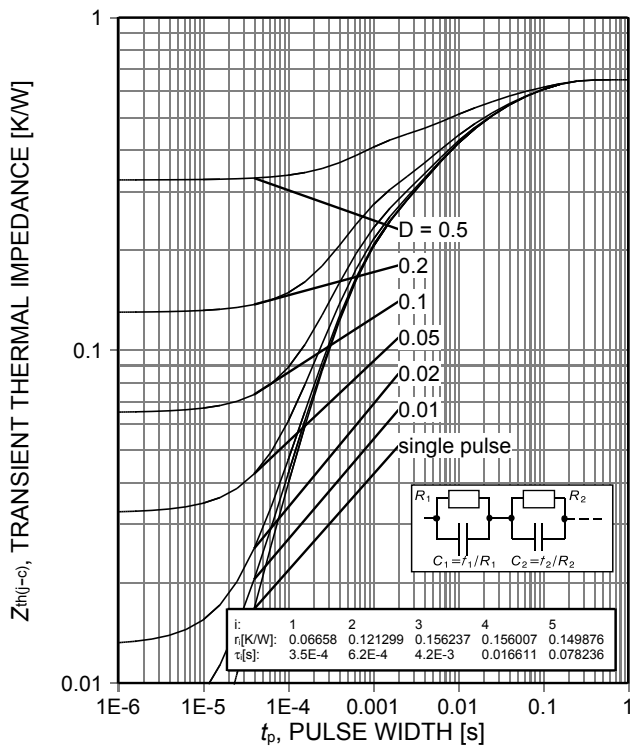


Figure 17. IGBT transient thermal impedance ( $D=t_p/T$ )

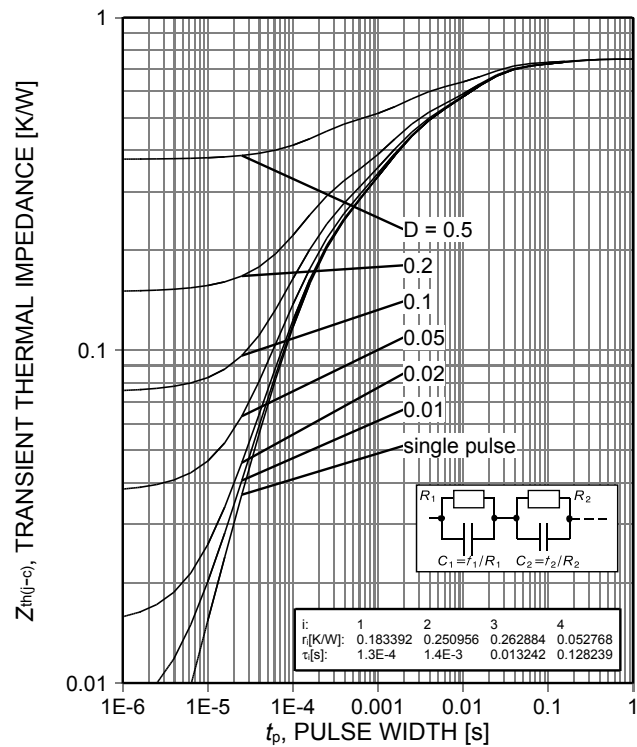


Figure 18. Diode transient thermal impedance as a function of pulse width ( $D=t_p/T$ )

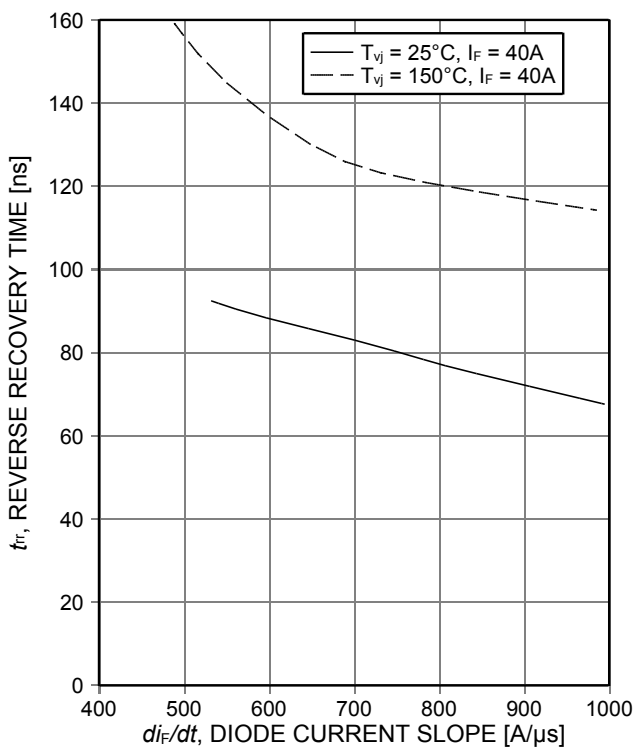


Figure 19. Typical reverse recovery time as a function of diode current slope ( $V_R=400V$ )

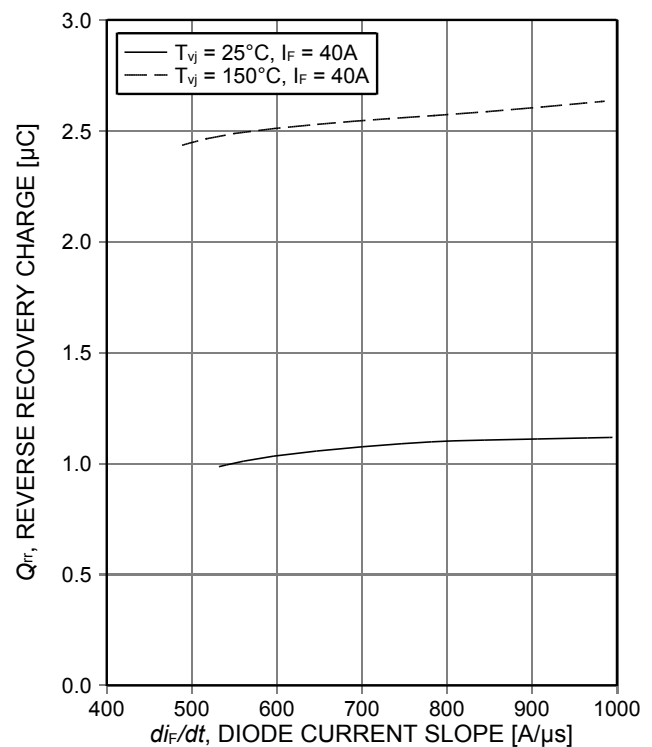


Figure 20. Typical reverse recovery charge as a function of diode current slope ( $V_R=400V$ )

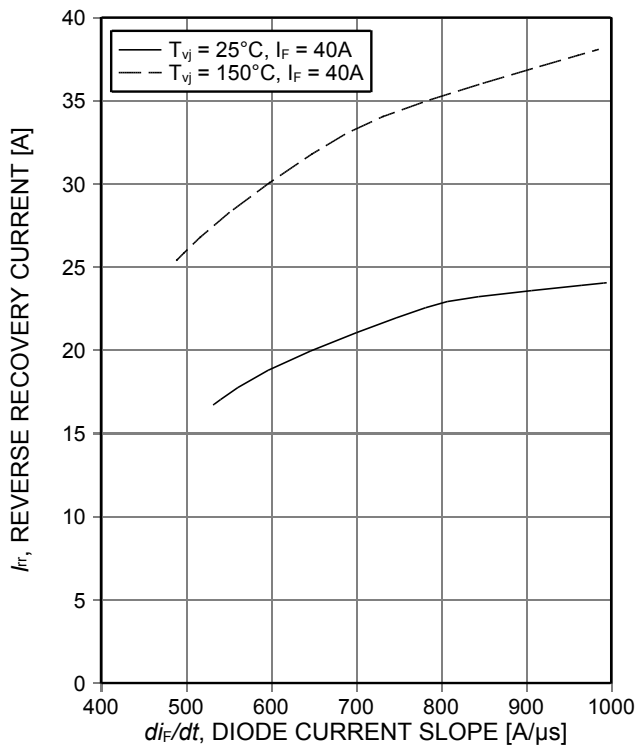


Figure 21. **Typical reverse recovery current as a function of diode current slope**  
( $V_R=400V$ )

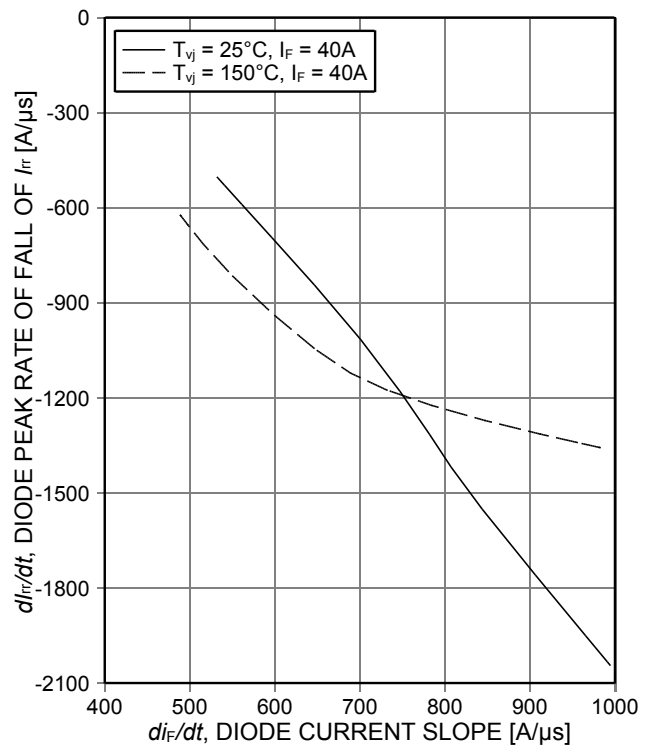


Figure 22. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**  
( $V_R=400V$ )

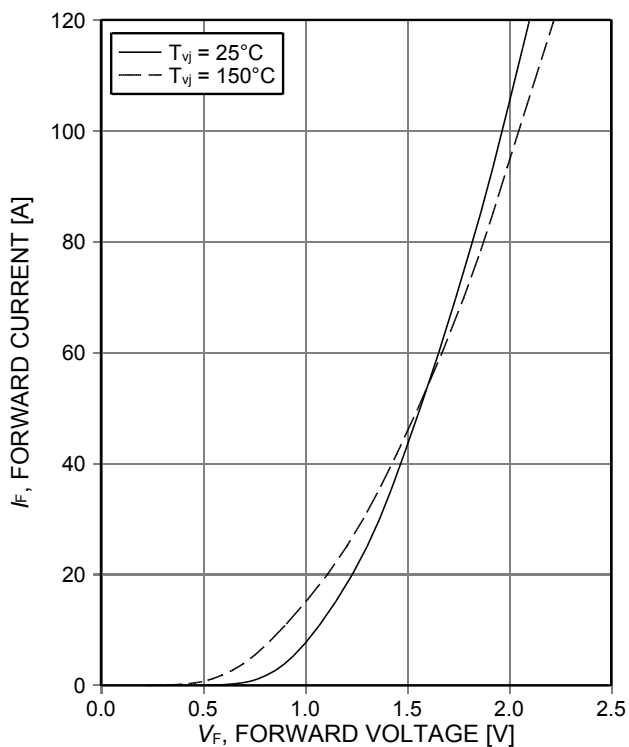


Figure 23. **Typical diode forward current as a function of forward voltage**

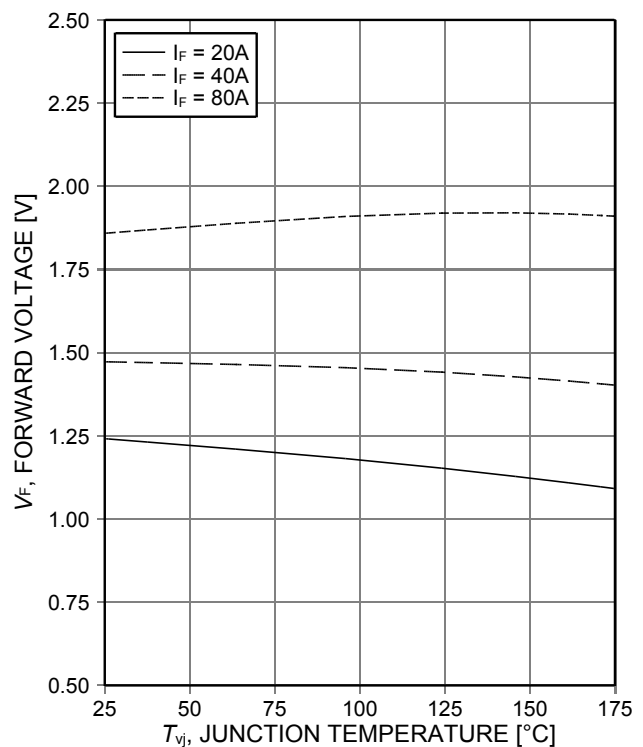
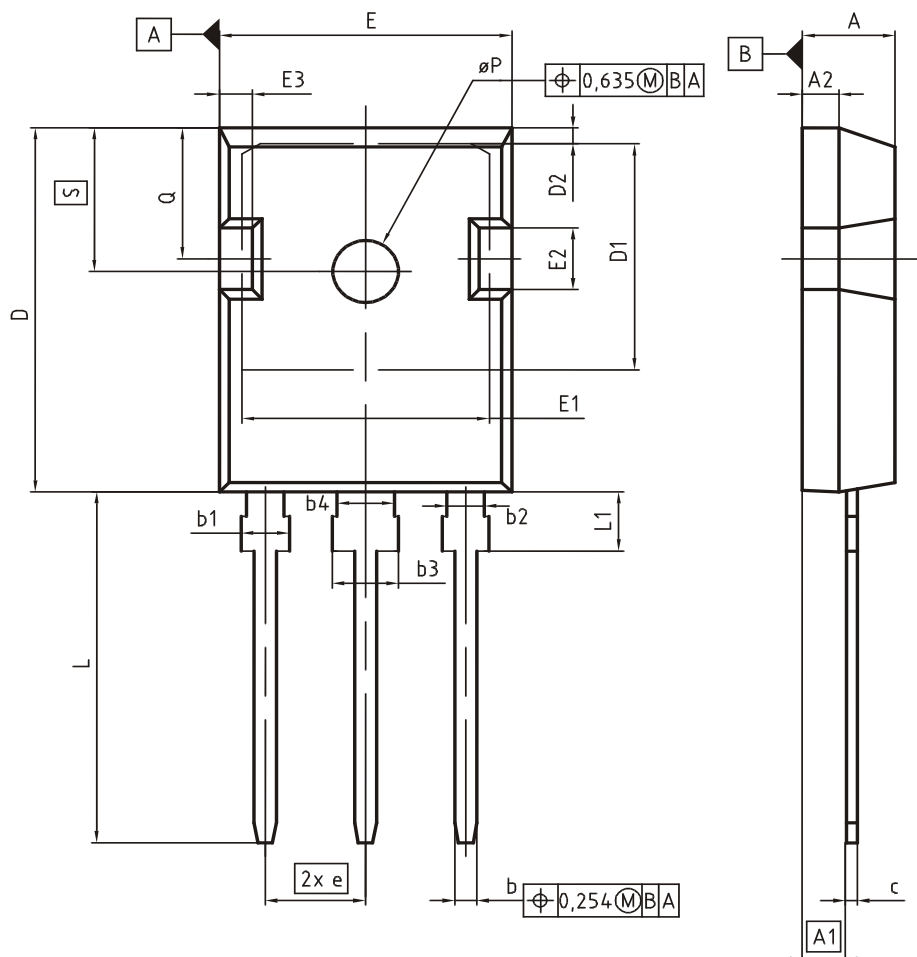
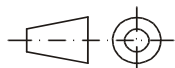


Figure 24. **Typical diode forward voltage as a function of junction temperature**

## Package Drawing PG-TO247-3



| DIM | MILLIMETERS |       | INCHES      |       |
|-----|-------------|-------|-------------|-------|
|     | MIN         | MAX   | MIN         | MAX   |
| A   | 4.83        | 5.21  | 0.190       | 0.205 |
| A1  | 2.27        | 2.54  | 0.089       | 0.100 |
| A2  | 1.85        | 2.16  | 0.073       | 0.085 |
| b   | 1.07        | 1.33  | 0.042       | 0.052 |
| b1  | 1.90        | 2.41  | 0.075       | 0.095 |
| b2  | 1.90        | 2.16  | 0.075       | 0.085 |
| b3  | 2.87        | 3.38  | 0.113       | 0.133 |
| b4  | 2.87        | 3.13  | 0.113       | 0.123 |
| c   | 0.55        | 0.68  | 0.022       | 0.027 |
| D   | 20.80       | 21.10 | 0.819       | 0.831 |
| D1  | 16.25       | 17.65 | 0.640       | 0.695 |
| D2  | 0.95        | 1.35  | 0.037       | 0.053 |
| E   | 15.70       | 16.13 | 0.618       | 0.635 |
| E1  | 13.10       | 14.15 | 0.516       | 0.557 |
| E2  | 3.68        | 5.10  | 0.145       | 0.201 |
| E3  | 1.00        | 2.60  | 0.039       | 0.102 |
| e   | 5.44 (BSC)  |       | 0.214 (BSC) |       |
| N   | 3           |       | 3           |       |
| L   | 19.80       | 20.32 | 0.780       | 0.800 |
| L1  | 4.10        | 4.47  | 0.161       | 0.176 |
| ØP  | 3.50        | 3.70  | 0.138       | 0.146 |
| Q   | 5.49        | 6.00  | 0.216       | 0.236 |
| S   | 6.04        | 6.30  | 0.238       | 0.248 |

|                                                                                                                     |
|---------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NO.</b><br>Z8B00003327                                                                                  |
| <b>SCALE</b><br>0 5 7.5mm                                                                                           |
| <b>EUROPEAN PROJECTION</b><br> |
| <b>ISSUE DATE</b><br>09-07-2010                                                                                     |
| <b>REVISION</b><br>05                                                                                               |

## Testing Conditions

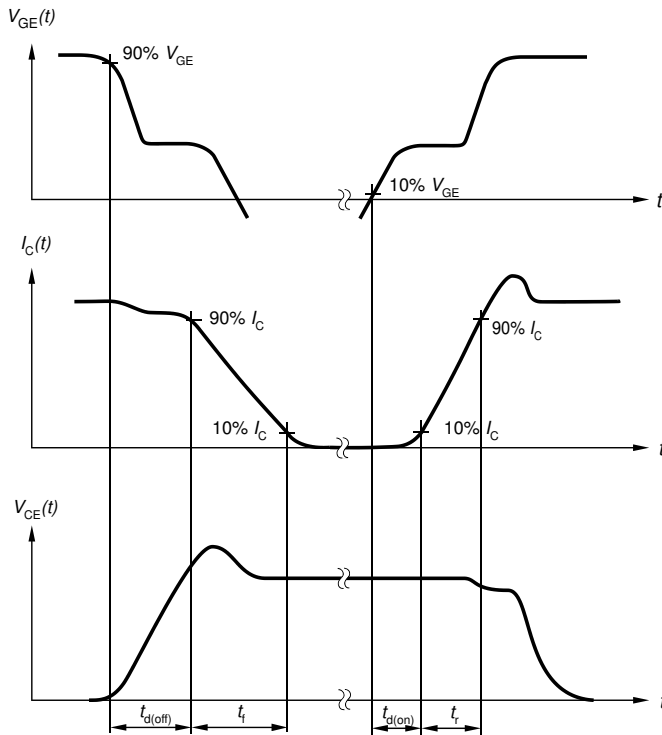


Figure A. Definition of switching times

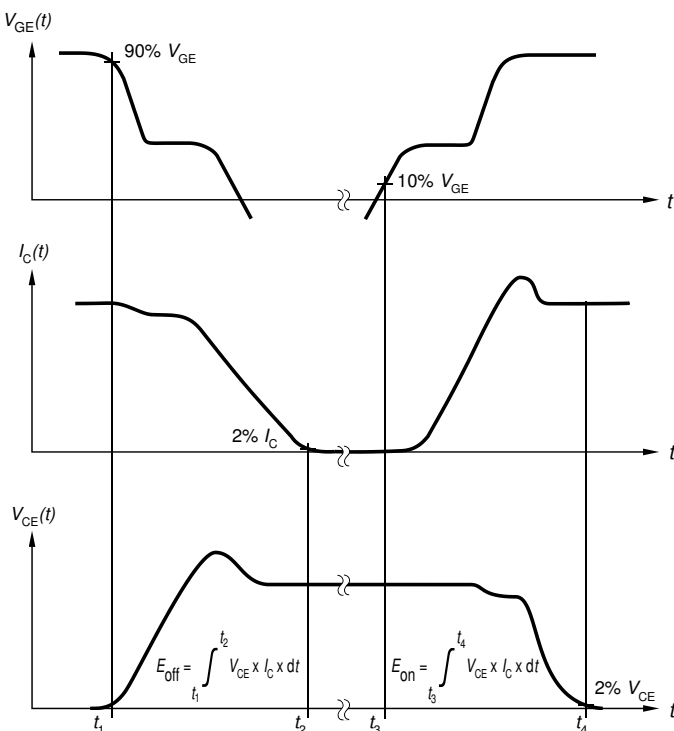


Figure B. Definition of switching losses

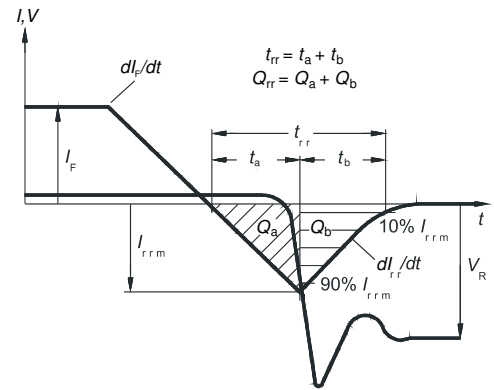


Figure C. Definition of diode switching characteristics

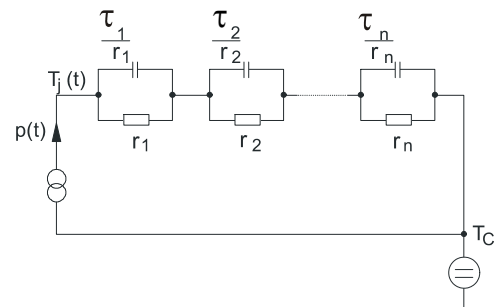


Figure D. Thermal equivalent circuit

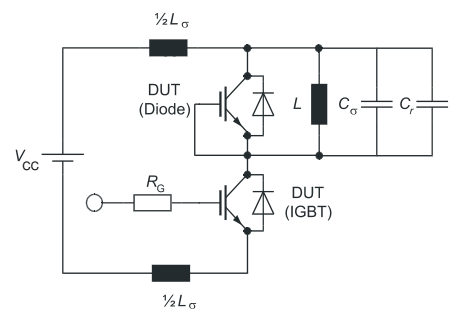


Figure E. Dynamic test circuit  
Parasitic inductance  $L_{\sigma}$ ,  
parasitic capacitor  $C_{\sigma}$ ,  
relief capacitor  $C_r$ ,  
(only for ZVT switching)

**Revision History**

IKW40N65ES5

**Revision: 2015-10-16, Rev. 2.2**

## Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 0.1      | 2015-05-26 | Target data sheet                            |
| 1.1      | 2015-08-12 | Preliminary data sheet                       |
| 2.1      | 2015-09-22 | Final data sheet                             |
| 2.2      | 2015-10-16 | Minor change $I_{c(VCE)}$ Fig. 3 and Fig. 4  |

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